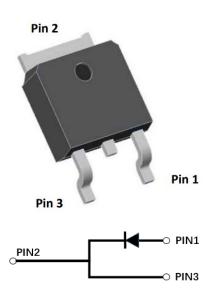


Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (135°C)}	11A
$Q_{\rm c}$	25nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, automotive battery chargers.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106506DQG2
Reverse voltage (repetitive peak) @ T;=25°C	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C			23
Continuous forward current @ T _c =135°C	I _F	Α	11
Continuous forward current @ T _c =160°C			6
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	65
Power Dissipation@ T _c =25°C	В	w	100
Power Dissipation@ T _c =110°C	P _{TOT}	VV	43
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	21
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

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■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	\/	V	I _F =6A, T _j =25°C	1.31	1.5
Forward voltage drop	V _F V	I _F =6A, T _j =175°C	1.65	-	
Poverse legicage gurrent			V _R =650V, T _j =25°C	0.5	25
Reverse leakage current	IR	I _R μΑ	V _R =650V, T _j =175°C	5	-
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C, $QC=\int_0^{VR}C(V)dV$	25	-
			V _R =0V, f=1MHZ	378	-
Total capacitance	С	pF	V _R =200V, f=1MHZ	51	-
			V _R =400V, f=1MHZ	49	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3	-

■Thermal Characteristics (Ta=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	1.49

■Typical Characteristics

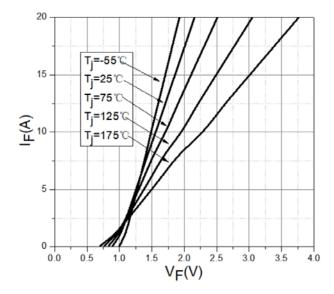


Figure 1. Forward Characteristics

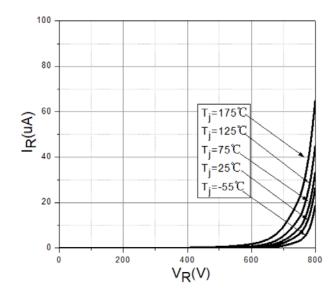
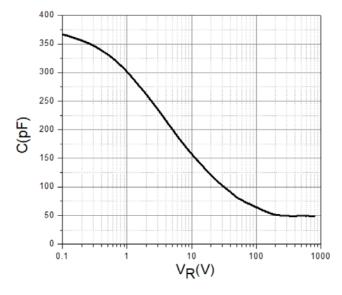


Figure 2. Reverse Characteristic





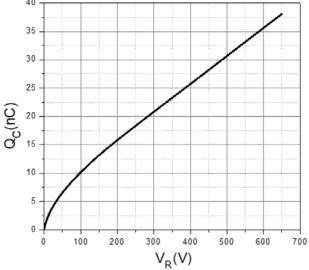


Figure 3. Capacitance vs. Reverse Voltage

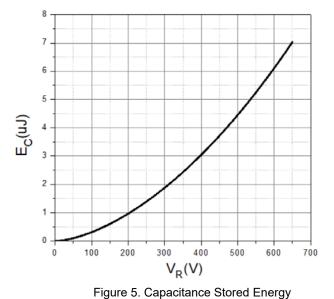
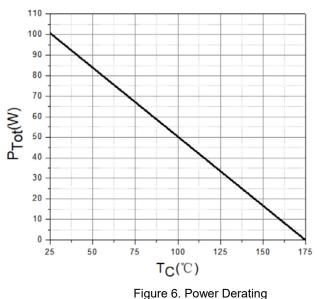
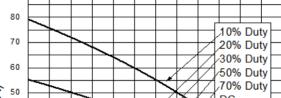
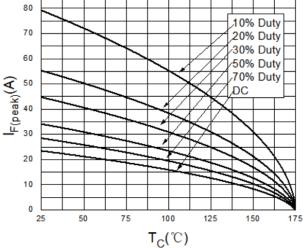


Figure 4. Total Capacitance Charge vs. Reverse Voltage







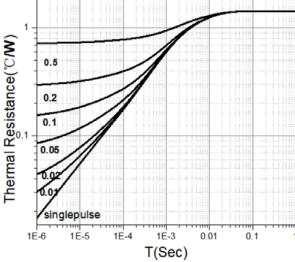


Figure 7. Current Derating

Figure 8. Transient Thermal Impedance

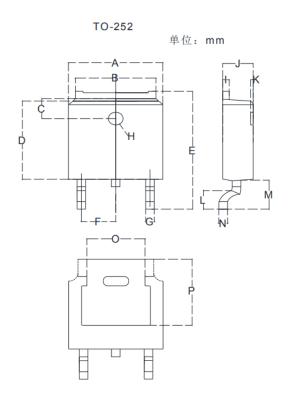
90







■Outline Dimensions



TO-252				
Dim	Min	Max		
Α	6.500	6.700		
В	5.100	5.460		
С	1.400	1.800		
D	6.000	6.200		
Е	10.000	10.400		
F	2.166	2.366		
G	0.660	0.860		
Н	Ф1.050	Ф1.350		
I	0.460	0.580		
J	2.200	2.400		
K	0	0.300		
L	0.890	2.290		
M	2.730	3.080		
N	0.430	0.580		
0	4.20	4.95		
Р	5.15	5.45		



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